

**1. Material**            Substrate      GaAs (N Type)  
                              Epitaxial Layer GaAs (P/N Type)

**2. Electrode**            N(Cathode) Side Gold Alloy  
                              P(Anode) Side Gold Alloy

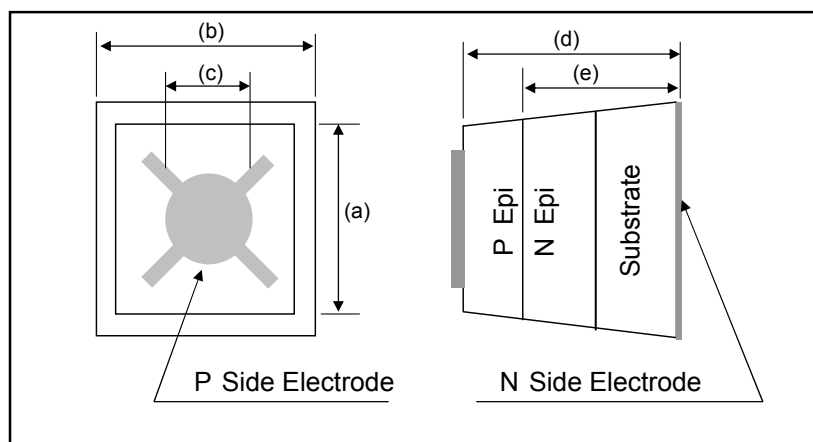
**3. Electro-Optical Characteristics**

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.5	1.6	V	IF=100mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	9.0	11		mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

- (a) Emission Area ----- 10.8mil x 10.8mil
- (b) Bottom Area ----- 11.8mil x 11.8mil
- (c) Bonding Pad ----- 130um
- (d) Chip Thickness ----- 11mil
- (e) Junction Height ----- 7.6mil



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